

BYW81HR

Aerospace 1 x 15 A and 2 x 15 A - 200 V fast recovery rectifier

Features

- Very small conduction losses
- Negligible switching losses
- High surge current capability
- High avalanche energy capability
- Hermetic packages
- Target radiation qualification:
 - 150 krad (Si) low dose rate
 - 1 Mrad high dose rate
- ESCC qualified

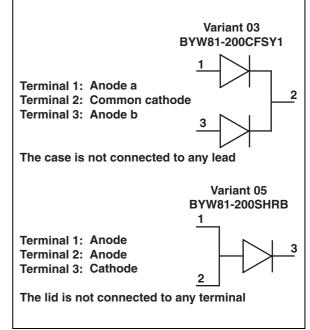
Description

Packaged in hermetic TO-254 or SMD.5, this device is intended for use in medium voltage, high frequency switching mode power supplies, high frequency DC to DC converters, and other aerospace applications.

The complete ESCC specification for this device is available from the European Space Agency web site. ST guarantees full compliance of qualified parts with such ESCC detailed specifications.







Order code	ESCC part number	Quality level	EPPL	Package	I _{F(AV)}	V _{RRM}	V _{F (max)}	T _{j(max)}
BYW81-200CFSY1	-	Engineering model	-	TO-254	2 x 15 A			
BYW81-200CFSYHRB	5103/029/03	ESCC flight	-	TO-254	2 x 15 A	200 V	1.15 V	150 °C
BYW81-200SHRB	5103/029/05	ESCC flight	Y	SMD.5	15 A			

1. Contact ST sales office for information about the specific conditions for products in die form and QML-Q versions.

1 Characteristics

Table 2.	Absolute	maximum	ratings
	/10001010	maximani	ratingo

Symbol	Characteristic	Value	Unit
I _{FSM}	Forward surge current ^{(1) (2)} Variant 05 Variant 03 (per diode) Variant 03 (per device)	250 250 500	A
V _{RRM}	Repetitive peak reverse voltage ⁽³⁾	200	V
I _O	Average output rectified current (50% duty cycle) ⁽²⁾⁽⁴⁾ Variant 05 Variant 03 (per diode) Variant 03 (per device)	15 15 30	A
I _{F(RMS)}	Forward rms current (per diode) ⁽²⁾ Variant 05 Variant 03 (per diode) Variant 03 (per device)	30 30 40	A
T _{OP}	Operating case temperature range ⁽⁵⁾	-55 to +150	°C
Τ _J	Junction temperature	+150	°C
T _{STG}	Storage temperature range ⁽⁵⁾	-55 to +150	°C
T _{SOL}	Soldering temperature TO-254 ⁽⁶⁾ SMD.5 ⁽⁷⁾	+260 +245	°C

1. Sinusoidal pulse of 10 ms duration

- 2. For variant 03 the "per device" ratings apply only when both cathode terminals are tied together.
- 3. Pulsed, duration 5 ms, F = 50 Hz
- 4. For $T_{case} \ge +110^{\circ}C$, derate linearly to 0 A at +150°C.
- 5. For devices with hot solder dip lead finish all testing performed at T_{amb} > +125 °C are carried out in a 100% inert atmosphere.
- 6. Duration 10 seconds maximum at a distance of not less than 1.5 mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
- 7. Duration 5 seconds maximum the same package shall not be resoldered until 3 minutes have elapsed.

Table 3.Thermal resistance

Symbol	Parameter	Value	Unit
	Junction to case		
R _{th (j-c)} ⁽¹⁾	All variants (per diode)	2.3	°C/W
U ,	Variant 03 (per device) ⁽²⁾	1.4	

1. Package mounted on infinite heatsink.

2. For variant 03 the "per device" ratings apply only when both cathode terminals are tied together.



Symbol	Characteristic	MIL-STD-750	Test conditions	Limits		Units
Symbol	Characteristic	test method	Test conditions	Min.	Max.	Units
I _R	Reverse current	4016	DC method, $V_R = 200 V$	-	20	μA
V _{F1} ⁽¹⁾	Forward voltage	4011	Pulse method, I _F = 10 A	-	1.0	V
V _{F2} ⁽¹⁾	Forward voltage	4011	Pulse method, I _F = 20 A	-	1.2	V
V _{BR}	Breakdown voltage	4021	I _R = 100 μA	200	-	V
С	Capacitance	4001	V _R = 10 V, F = 1 MHz	-	220	pF
t _{rr}	Reverse recovery time	4031	I _F = 1 A, V _R = 30 V, dI _F /dt = -50 A/μs	-	40	ns
$Z_{th(j-c)}^{(2)}$	Relative thermal impedance, junction to case	3101	$I_H = 15$ to 40 A, t _H = 50 ms $I_M = 50$ mA, t _{md} = 100 μs	Calculat	e $\Delta V_{F}^{(3)}$	°C/W

Table 4.	Electrical measurements at ambiant temperature (per diode), T _{amb} = 22 ±3 °C
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1. Pulse width $\leq 300 \mu s, \, duty \, cycle \leq 2\%$

2. Performed only during screening tests parameter drift values (initial measurements), go-no-go.

3. The limits for ΔVF shall be defined by the manufacturer on every lot in accordance with MIL-STD-750 Method 3101 and shall guarantee the $R_{th(j-c)}$ limits specified in maximum ratings.

Table 5.	Electrical measurements	at high and low	v temperatures (per d	liode)

Symbol Characteristic		MIL-STD-750	Test conditions ⁽¹⁾	Limits		Units
Symbol	Characteristic	test method	rest conditions.	Min.	Max.	Units
I _R	Reverse current	4016	T _{case} = +125 (+0, -5) °C DC method, V _R = 200 V	-	10	mA
V ⁽²⁾	V _{F1} ⁽²⁾ Forward voltage 4011		$T_{case} = +125 (+0, -5) °C$ pulse method, I _F = 10 A	-	0.85	V
¥ F1`´			$T_{case} = +55 (+0, -5) ^{\circ}C$ pulse method, I _F = 10 A	-	1.15	V

1. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

2. Pulse width \leq 300µs, duty cycle \leq 2%



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK[®] is an ST trademark.

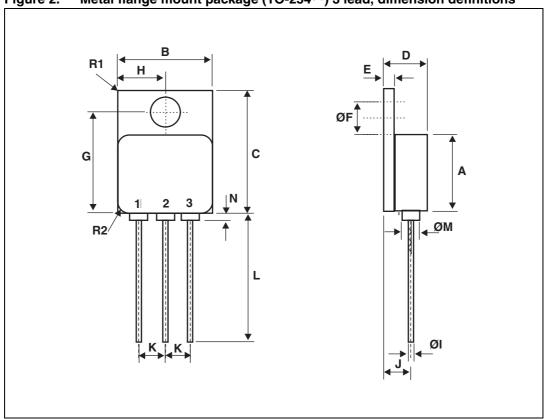


Figure 2. Metal flange mount package (TO-254^(a)) 3 lead, dimension definitions



a. The terminal identification is specified by the device configuration. See *Figure 1* for terminal connections

Defenses	Dimension	in millimetres	Dimlensior	n in inches
Reference -	Min.	Max.	Min.	Max.
А	13.59	13.84	0.535	0.545
В	13.59	13.84	0.535	0.545
С	20.07	20.32	0.790	0.800
D	6.3	6.7	0.248	0.264
E	1	3.9	0.039	0.154
ØF	3.5	3.9	0.138	0.154
G	16.89	17.4	17.4 0.665	
н	6.86	BSC	0.270	BSC
ØI ⁽¹⁾	0.89	1.14	0.035	0.045
J	3.81	BSC	0.150	BSC
к	3.81 BSC		0.150	BSC
L	12.95	14.5	0.510	0.571
ØM	3.05	5 Тур.	0.120) Тур.
Ν	-	0.71	-	0.028
R1 ⁽²⁾	-	1	-	0.039
R2 ⁽³⁾	1.6	5 Тур.	0.0	65

 Table 6.
 Metal flange mount package (TO-254) 3-lead, dimension values

1. 3 locations

2. Radius of heatsink flange corner - 4 locations

3. Radius of body corner - 4 locations



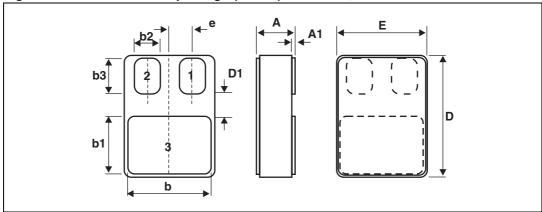


Figure 3. Surface mount package (SMD.5) 3-terminal, dimension definitions

Table 7. Surface mount package (SMD.5) 3-terminal, dimension values

Reference	Dimension in	n millimetres	Dimlension in inches		
Reierence	Min. Max.		Min.	Max.	
A	2.84	3.15	0.112	0.124	
A1	0.25	0.51	0.010	0.20	
b	7.13	7.39	0.281	0.291	
b1	5.58	5.84	0.220	0.230	
b2 ⁽¹⁾	2.28	2.54	0.090	0.100	
b3 ⁽¹⁾	2.92	3.18	0.115	0.125	
D	10.03	10.28	0.395	0.405	
D1 ⁽¹⁾	0.76	-	0.030	-	
E	7.39	7.64	0.291	0.301	
e ⁽¹⁾	1.91	BSC	0.0)75	

1. 2 locations



3 Ordering information

Table 8.Ordering information⁽¹⁾

Order code	ESCC part number	Quality level	EPPL	Package	Lead finish	Marking	Mass	Packing
BYW81-200CFSY1	-	Engineering model	-	TO-254	Gold	BYW81200CFSY1 + BeO	10 a	
BYW81- 200FSYHRB	5103/029/03	ESCC flight	-	TO-254	Solder dip	510302901 + BeO	10 g	Strip pack
BYW81-200SHRB	5103/029/05	ESCC flight	Y	SMD.5	Gold	510302905	2.0 g	

1. Contact ST sales office for information about the specific conditions for products in die form and QML-Q versions.



4 Revision history

Table 9.Document revision history

Date	Revision	Changes
03-Nov-2010	1	First issue.



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